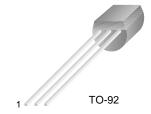


### **PN3568**

## **NPN General Purpose Amplifier**

• This device is designed for general purpose, medium power amplifiers and switches requiring collector currents to 500mA.



1. Emitter 2. Base 3. Collector

## **Absolute Maximum Ratings\*** T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V
V <sub>CBO</sub>	Collector-Base Voltage	80	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	1.0	Α
T <sub>J,</sub> T <sub>STG</sub>	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaird.

- These ratings are based on a maximum junction temperature of 150 degrees C.
   These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

## **Electrical Characteristics** $T_A$ =25°C unless otherwise noted

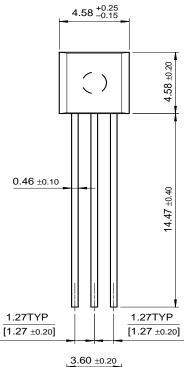
Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Chara	cteristics			•	
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage *	$I_C = 30 \text{mA}, I_B = 0$	60		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 100\mu A, I_E = 0$	80		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	5.0		V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = 40V, I <sub>E</sub> = 0 V <sub>CB</sub> = 40V, I <sub>E</sub> = 0, T <sub>A</sub> = 75°C		50 5.0	nA μA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 4V, I_{C} = 0$		25	nA
On Chara	cteristics	•			•
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 1.0V, I_{C} = 30mA$	40		
		$V_{CE} = 1.0V, I_{C} = 150mA$	40	120	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA		0.25	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> = 1.0V, I <sub>C</sub> = 150mA		1.1	V
Small Sign	nal Characteristics			•	
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 10V, f = 1.0MHz		20	pF
C <sub>ib</sub>	Input Capacitance	V <sub>EB</sub> = 0.5V, f = 1.0MHz		80	
h <sub>fe</sub>	Small Signal Current Gain	$I_C = 50 \text{mA}, V_{CE} = 10 \text{V}, f = 20 \text{MHz}$	3.0	30	
Pulse Test: Pu	llse Width < 300ms, Duty Cycle < 2.0%	1	1		

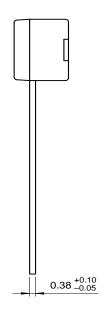
Pulse Test: Pulse Width ≤ 300ms, Duty Cycle ≤ 2.0%

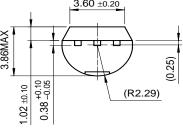
Thermal Characteristics T <sub>A</sub> =25°C unless otherwise noted			
Symbol	Parameter	Max.	Units
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case 83.3 °C/		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

# **Package Dimensions**

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EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
E <sup>2</sup> CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	I <sup>2</sup> C <sup>TM</sup>	$OCX^{TM}$	RapidConfigure™	UHC™
Across the board.	. Around the world.™	OCXPro™	RapidConnect™	UltraFET <sup>®</sup>
The Power Franchise™		OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	$VCX^{TM}$
Programmable Ad	ctive Droop™	OPTOPLANAR™	SMART START™	

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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